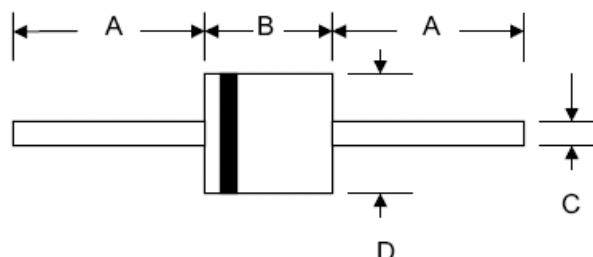


Technical Data
Data Sheet N0450, Rev. A

Green Products

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



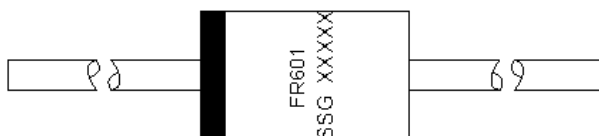
Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 2.1 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Epoxy: UL 94V-O rate flame retardant

R-6				
Dim	Min	Max	Min	Max
A	25.4	—	1.000	—
B	8.60	9.10	0.338	0.358
C	1.20	1.30	0.047	0.051
D	8.60	9.10	0.338	0.358
	In mm		In inch	

Marking Diagram:

Where XXXXX is YYWWL



FR601 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
FR601-FR607	R-6 (Pb-Free)	500pcs / box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

- China - Germany - Korea - Singapore - United States ●
- <http://www.smc-diodes.com> - sales@smc-diodes.com ●



FR601-FR607
6.0A FAST RECOVERY RECTIFIER

Technical Data
Data Sheet N0450, Rev. A

Green Products

Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	FR601	FR602	FR603	FR604	FR605	FR606	FR607	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @ $T_A = 55^{\circ}\text{C}$	I_O	6.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200							A
Forward Voltage @ $I_F = 6.0\text{A}$	V_{FM}	1.2							V
Peak Reverse Current @ $T_A = 25^{\circ}\text{C}$ At Rated DC Blocking Voltage @ $T_A = 100^{\circ}\text{C}$	I_{RM}	10 200							μA
Reverse Recovery Time (Note 2)	t_{rr}	150				250	500		nS
Typical Junction Capacitance (Note 3)	C_j	100							pF
Operating Temperature Range	T_j	-65 to +125							$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150							$^{\circ}\text{C}$

***Glass passivated forms are available upon request**

- Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured with $I_F = 0.5\text{A}$, $I_R = 1.0\text{A}$, $I_{RR} = 0.25\text{A}$. See figure 5.
3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

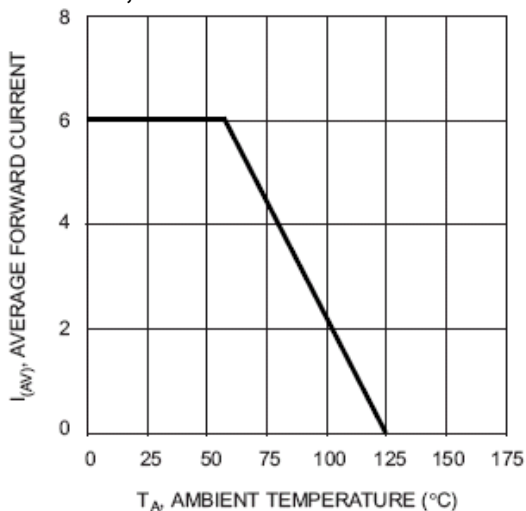


Fig. 1, Typical Forward Current Derating Curve

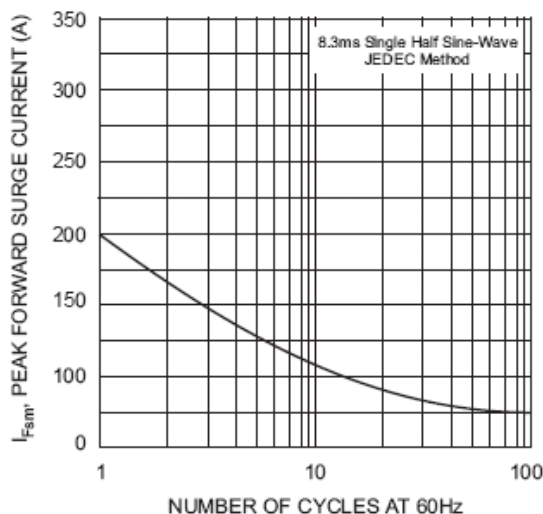


Fig. 2 Max Non-Repetitive Peak Surge Current

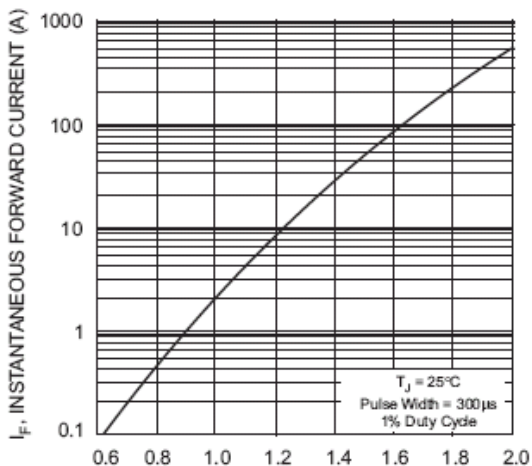


Fig. 3, Typical Instantaneous Forward Characteristics

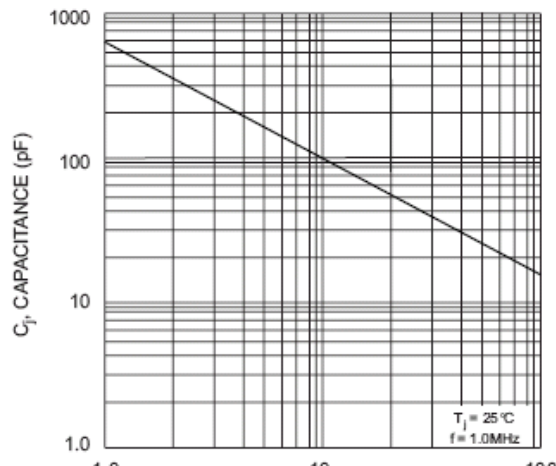
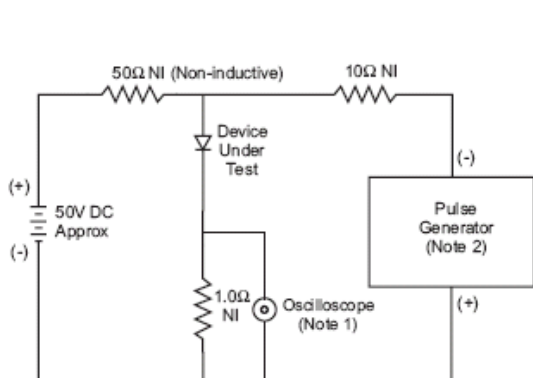


Fig. 4 Typical Junction Capacitance



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.

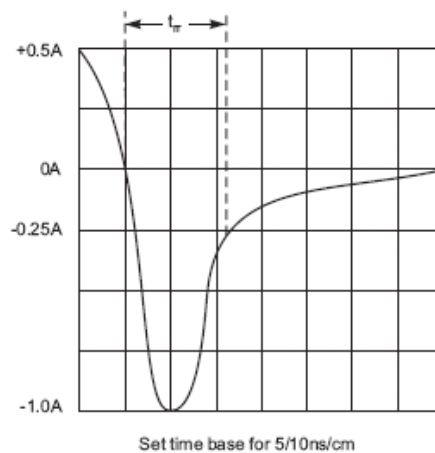


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit



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